

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
-30V	23mΩ@-10V	-11A
	36mΩ@-4.5V	

## Feature

- Advanced trench process technology
- High Density Cell Design For Ultra Low On-Resistance

## Application

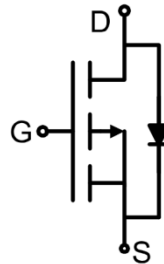
- Load Switch
- Battery Switch
- Power management

## Package



SOP-8

## Circuit diagram



## Marking



### Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	-11	A
Pulsed Drain Current	I <sub>DM</sub>	-50	A
Power Dissipation	P <sub>D</sub>	3.0	W
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	40	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

### Electrical characteristics (T<sub>A</sub>=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-30			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V			-1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1		-3	V
Drain-source on-resistance <sup>1)</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -10A		16	23	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -5A		21	36	
<b>Dynamic characteristics<sup>2)</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz		1130		pF
Output Capacitance	C <sub>oss</sub>			240		
Reverse Transfer Capacitance	C <sub>rss</sub>			155		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -10A		18		nC
Gate-Source Charge	Q <sub>gs</sub>			5.5		
Gate-Drain Charge	Q <sub>gd</sub>			3.3		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -1A, R <sub>GEN</sub> = 3Ω		8.7		nS
Turn-on rise time	t <sub>r</sub>			8.5		
Turn-off delay time	t <sub>d(off)</sub>			18		
Turn-off fall time	t <sub>f</sub>			7		
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.1A			-1.2	V

Notes:

- 1) Pulse Test: Pulse Width < 300μs, Duty Cycle ≤2%.
- 2) Guaranteed by design, not subject to production testing.

## Typical Characteristics

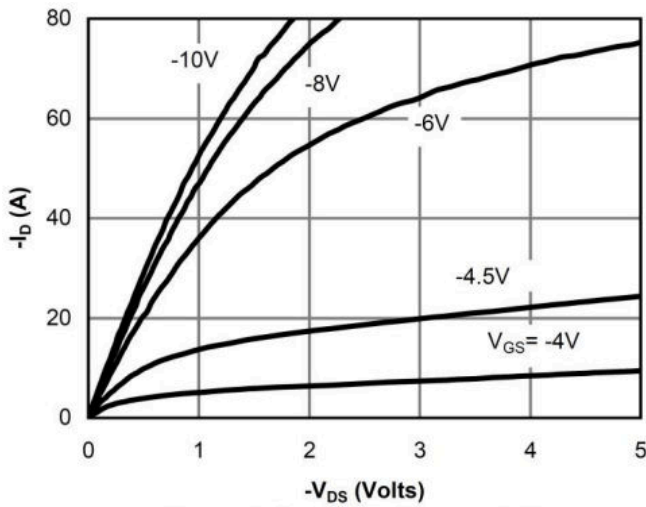


Figure 1: On-Region Characteristics

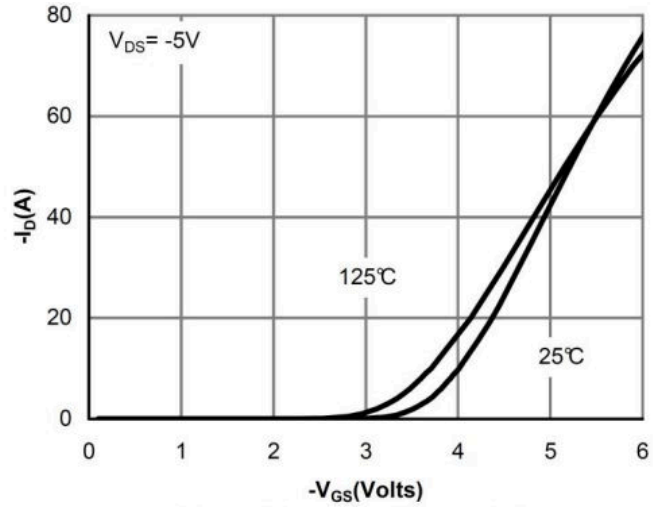


Figure 2: Transfer Characteristics

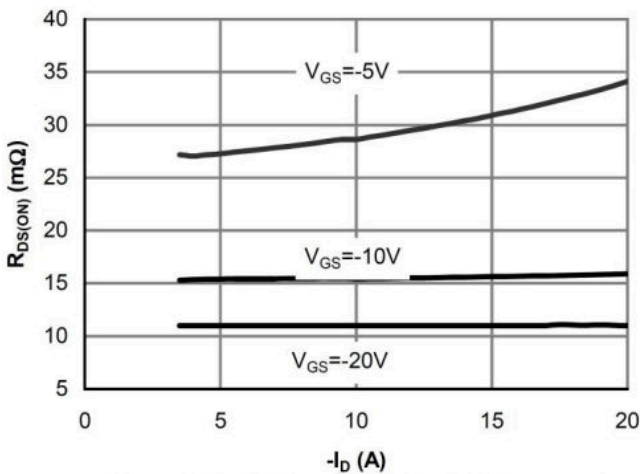


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

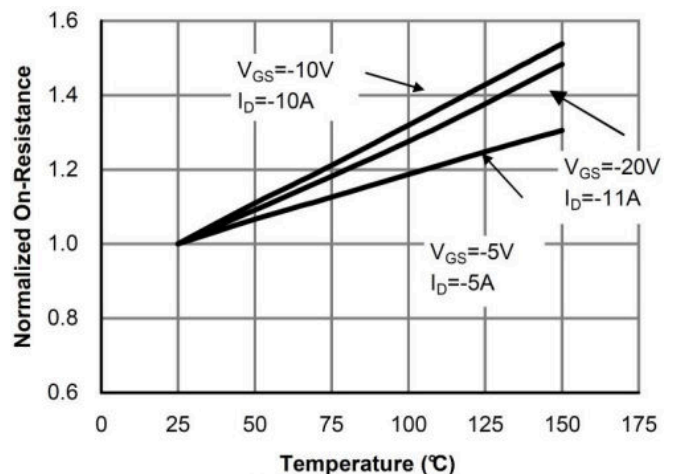


Figure 4: On-Resistance vs. Junction Temperature

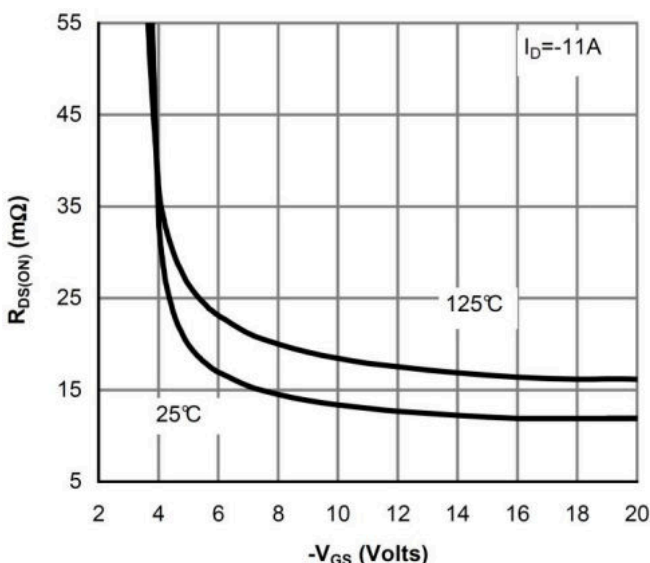


Figure 5: On-Resistance vs. Gate-Source Voltage

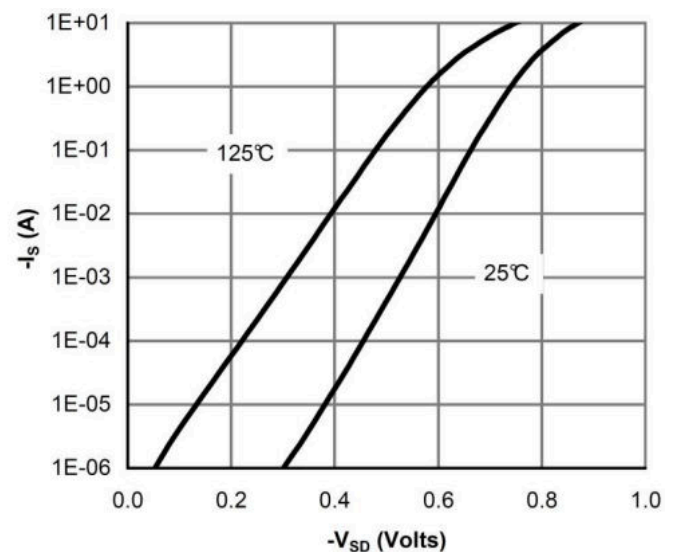


Figure 6: Body-Diode Characteristics

## Typical Characteristics

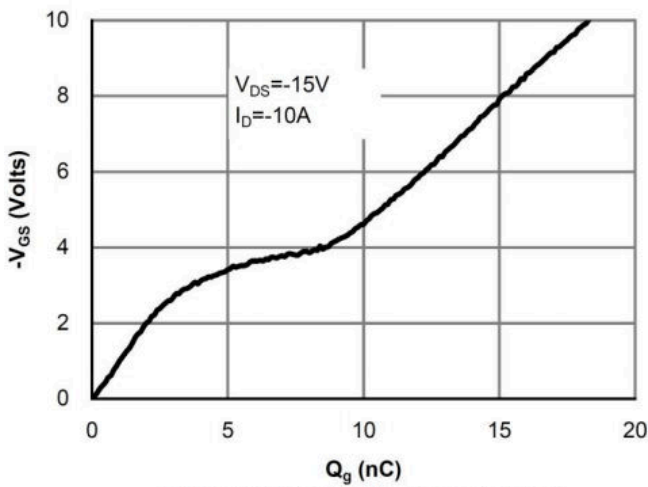


Figure 7: Gate-Charge Characteristics

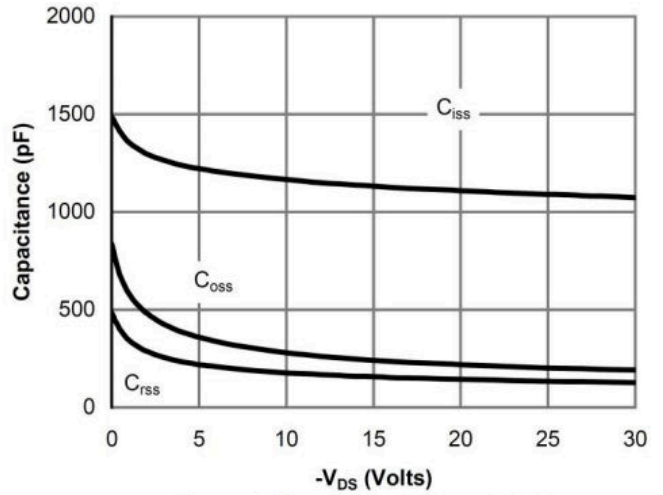


Figure 8: Capacitance Characteristics

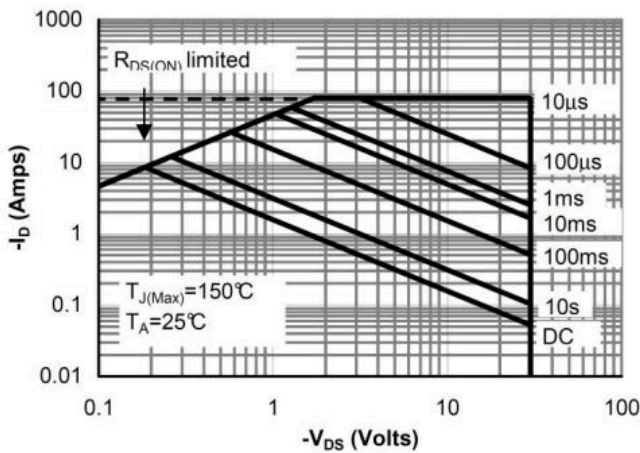


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

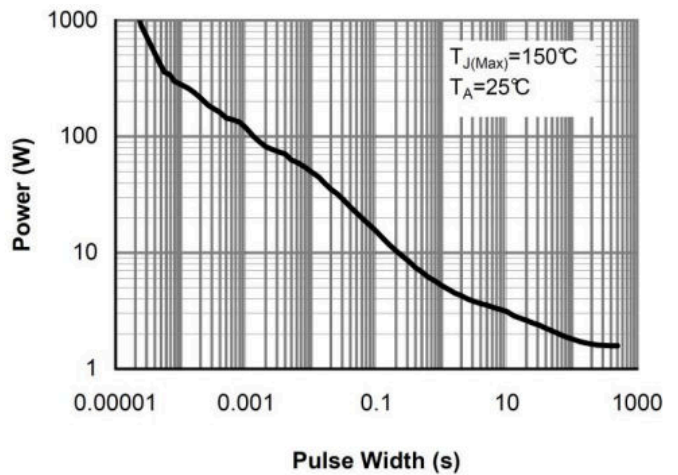


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

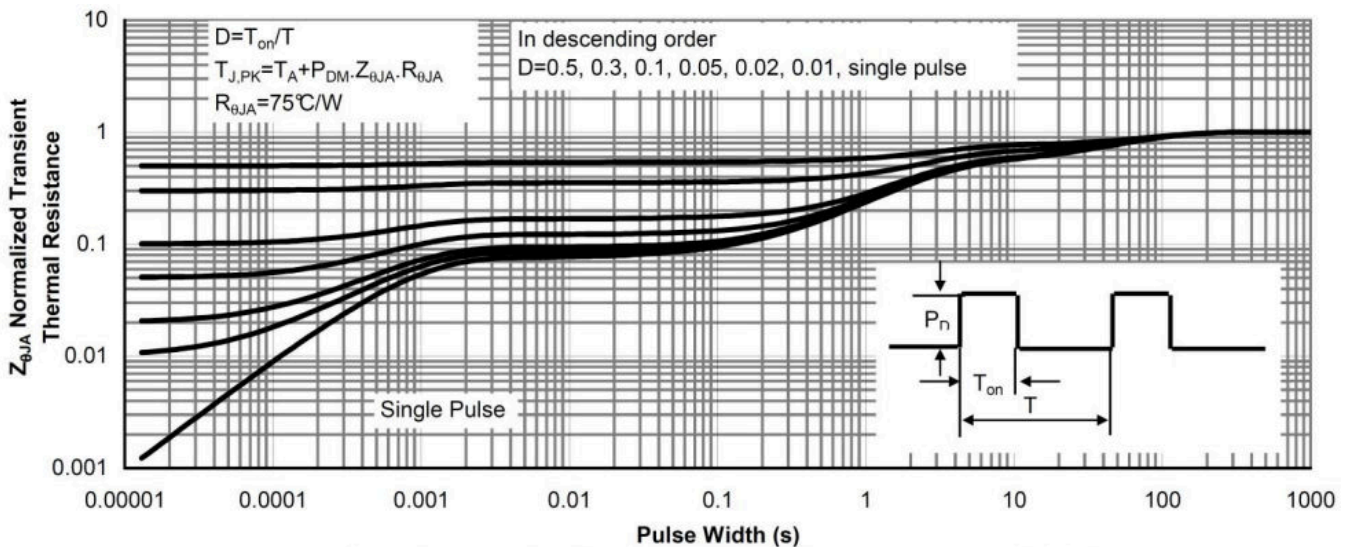
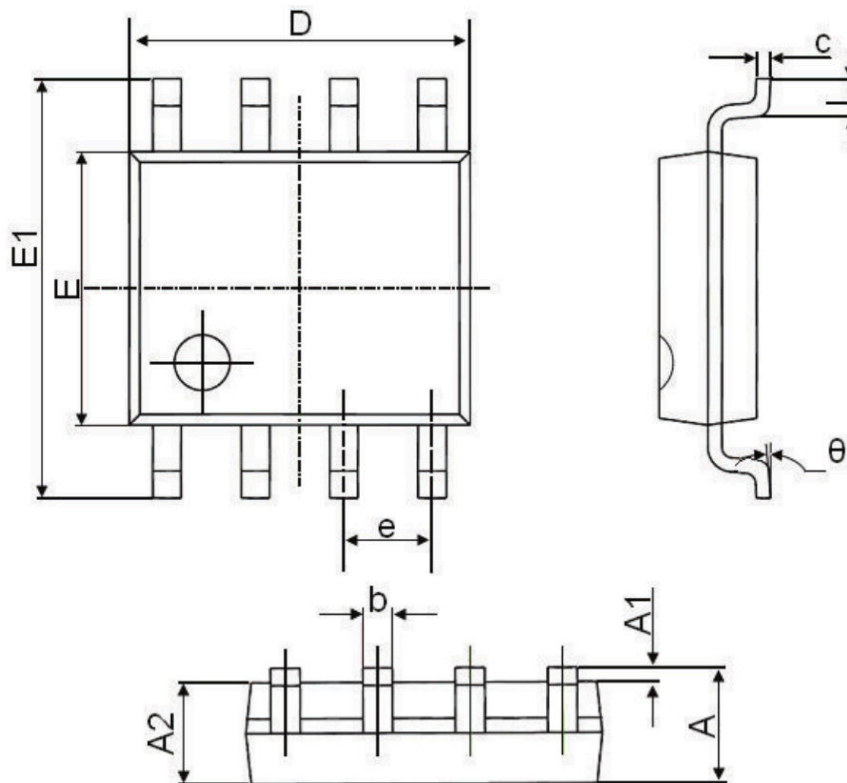


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)

## SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
theta	0°	8°	0°	8°